Yukihiro Harada

List of Publications by Citations

49 papers	466 citations	14 h-index	20 g-index
64 ext. papers	532 ext. citations	2.6 avg, IF	3.57 L-index

#	Paper	IF	Citations
49	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. *Physical Review B*, **2011**, 84,	3.3	41
48	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. *Physical Review B* , **2013**, 87,	3.3	40
47	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. *Applied Physics Express*, **2011**, 4, 062001	2.4	36
46	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. *Physical Review B*, **2015**, 91,	3.3	29
45	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. *Physical Review B*, **2012**, 86,	3.3	29
44	Effect of internal electric field on InAs/GaAs quantum dot solar cells. *Journal of Applied Physics*, **2014**, 115, 083510	2.5	27
43	Assessing the Nature of the Distribution of Localised States in Bulk GaAsBi. *Scientific Reports*, **2018**, 8, 6457	4.9	24
42	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. *Journal of Applied Physics*, **2013**, 113, 223511	2.5	22
41	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. *Physical Review B*, **2008**, 77,	3.3	20
40	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. *Physical Review B*, **2016**, 93,	3.3	16
39	Anisotropic magneto-optical effects in one-dimensional diluted magnetic semiconductors. *Physical Review B*, **2006**, 74,	3.3	16
38	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. *Applied Physics Letters*, **2014**, 104, 041907	3.4	14
37	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. *Scientific Reports*, **2017**, 7, 5865	4.9	14
36	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. *Journal of Applied Physics*, **2014**, 115, 233512	2.5	14
35	Hot-carrier solar cells using low-dimensional quantum structures. *Applied Physics Letters*, **2014**, 105, 171904	3.4	14
34	Extremely uniform bound exciton states in nitrogen □doped GaAs studied by photoluminescence spectroscopy in external magnetic fields. *Journal of Applied Physics*, **2011**, 110, 083522	2.5	9
33	Thermal annealing effects on ultra-violet luminescence properties of Gd doped AlN. *Journal of Applied Physics*, **2015**, 117, 163105	2.5	8

32	Increasing conversion efficiency of two-step photon up-conversion solar cell with a voltage booster hetero-interface. *Scientific Reports*, **2018**, 8, 872	4.9	8
31	Two-step photocurrent generation enhanced by miniband formation in InAs/GaAs quantum dot superlattice intermediate-band solar cells. *Applied Physics Letters*, **2017**, 110, 193104	3.4	7
30	Hot-carrier generation and extraction in InAs/GaAs quantum dot superlattice solar cells. *Semiconductor Science and Technology*, **2019**, 34, 094003	1.8	7
29	Intermediate band photovoltaics based on interband□intraband transitions using In0.53Ga0.47As/InP superlattice. *Progress in Photovoltaics: Research and Applications*, **2011**, 21, n/a-n/a	6.8	7
28	Bound biexciton luminescence in nitrogen □doped GaAs. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 464-467	1.3	7
27	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. *Physical Review B*, **2017**, 96,	3.3	6
26	Photocarrier transport dynamics in InAs/GaAs quantum dot superlattice solar cells using time-of-flight spectroscopy. *Physical Review B*, **2016**, 94,	3.3	6
25	Energy Conversion Efficiency of Solar Cells. *Green Energy and Technology*, **2019**,	0.6	5
24	Control of stacking direction and optical anisotropy in InAs/GaAs quantum dots by In flux. *Journal of Applied Physics*, **2013**, 114, 033517	2.5	5
23	Improving laser cooling efficiencies of Yb-doped yttrium aluminum garnet by utilizing non-resonant anti-Stokes emission at high temperatures. *Optics Express*, **2019**, 27, 34961-34973	3.3	5
22	Effects of rapid thermal annealing on two-dimensional delocalized electronic states of the epitaxial N □doped layer in GaAs. *Applied Physics Letters*, **2016**, 108, 111905	3.4	4
21	Hot-carrier generation in a solar cell containing InAs/GaAs quantum-dot superlattices as a light absorber. *Applied Physics Express*, **2018**, 11, 082303	2.4	3
20	Anisotropic magneto-optical effects in CdTe/Cd0.75Mn0.25Te quantum wire structures. *Physical Review B*, **2008**, 78,	3.3	3
19	Anisotropic exchange interaction caused by hole-spin reorientation in (CdTe)0.5(Cd0.75Mn0.25Te)0.5 tilted superlattices grown on Cd0.74Mg0.26Te(001) vicinal surface. *Journal of Crystal Growth*, **2005**, 275, e2221-e2224	1.6	3
18	Polarization characteristics of electroluminescence and net modal gain in highly stacked InAs/GaAs quantum-dot laser devices. *Journal of Applied Physics*, **2016**, 120, 134313	2.5	3
17	An energy transfer accompanied by phonon absorption in ytterbium-doped yttrium aluminum perovskite for optical refrigeration. *Applied Physics Letters*, **2020**, 117, 041104	3.4	2
16	Bandwidth enhancement in an InGaN/GaN three-section superluminescent diode for optical coherence tomography. *Applied Physics Letters*, **2020**, 117, 061106	3.4	2
15	Bound-to-continuum intraband transition properties in InAs/GaAs quantum dot superlattice solar cells. *Applied Physics Express*, **2019**, 12, 125008	2.4	2

14	Polarization controlled emisson from closely stacked InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1492-1495		1
13	Resonant indirect excitation of Gd3+ in AlN thin films. *Journal of Applied Physics*, **2014**, 115, 173508	2.5	1
12	High-resolution optical coherence tomography using broadband light source with strain-controlled InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 2473-2476		1
11	Interaction between conduction-band edge and nitrogen-related localized levels in nitrogen □ -doped GaAs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 365-367		1
10	Statistical fluctuation of magnetization in Mn-composition modulated Cd1□MnxTe quantum wires. *Journal of Applied Physics*, **2010**, 107, 043521	2.5	1
9	Valence-band mixing induced by sp-d exchange interaction in CdMnTe quantum wires. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 667-670		1
8	Properties of Anti-Stokes Photoluminescence and Ideal Laser Cooling Performance in Yb-Doped Yttrium Aluminum Garnet Thin Film. *Zairyo/Journal of the Society of Materials Science, Japan*, **2020**, 69, 727-732	0.1	1
7	Fundamental Device Characteristics of Hot Carrier Solar Cell Using InAs/GaAs Quantum Dot Superlattices.. *Zairyo/Journal of the Society of Materials Science, Japan*, **2017**, 66, 629-633	0.1	
6	Actual Calculation of Solar Cell Efficiencies. *Green Energy and Technology*, **2019**, 81-137	0.6	
5	Ideal Laser Cooling Efficiency Utilizing Anti-Stokes Luminescence in Yb-Doped Yttrium Aluminum Garnet Powder Crystals. *Zairyo/Journal of the Society of Materials Science, Japan*, **2019**, 68, 762-766	0.1	
4	Near-field photoluminescence spectroscopy of CdTe/Cd0.75Mn0.25Te tilted superlattices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 262-265		
3	Anisotropic linear-polarization luminescence in CdTe/CdMnTe quantum wires. *Journal of Luminescence*, **2009**, 129, 1448-1453	3.8	
2	Yb-doped YAlO thin films with a self-organized columnar structure and their anti-Stokes photoluminescence properties. *AIP Advances*, **2022**, 12, 025110	1.5	
1	Analysis of Optical Waveguide Mode in Closely-Stacked InAs/GaAs Quantum Dot Semiconductor Optical Amplifiers. *Zairyo/Journal of the Society of Materials Science, Japan*, **2015**, 64, 685-689	0.1	